

Improved Quad SPST CMOS Analog Switches

DESCRIPTION

The DG444B, DG445B are monolithic quad analog switches designed to provide high speed, low error switching of analog and audio signals. The DG444B, DG445B are upgrades to the original DG444, DG445.

Combining low on-resistance (45 Ω , typ.) with high speed (t_{on} 120 ns, typ.), the DG444B, DG445B are ideally suited for data acquisition, communication systems, automatic test equipment, or medical instrumentation. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

The DG444B, DG445B are built using Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

When on, each switch conducts equally well in both directions and blocks input voltages to the supply levels when off.

BENEFITS

- Low signal errors and distortion
- Reduced power supply consumption
- Faster throughput
- Reduced pedestal errors
- Simple interfacing

FEATURES

- Low on-resistance: 45 Ω
- Low power consumption: 1 mW
- Fast switching action - t_{on} : 120 ns
- Low charge injection
- TTL/CMOS-compatible logic
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

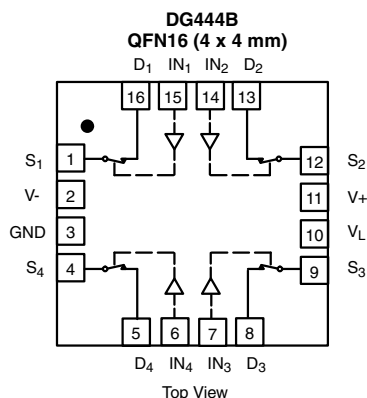
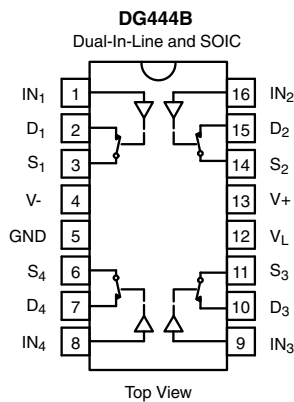


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Audio switching
- Data acquisition
- Sample-and-hold circuits
- Communication systems
- Automatic test equipment
- Medical instruments

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE

LOGIC	DG444B	DG445B
0	On	Off
1	Off	On

Note

- Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.4 V

ORDERING INFORMATION

TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to +85 °C	16-pin narrow SOIC	DG444BDY-E3
		DG444BDY-T1-E3
		DG445BDY-E3
		DG445BDY-T1-E3
	16-pin QFN 4 x 4 mm (variation 1)	DG444BDN-T1-E4
		DG445BDN-T1-E4



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
V+ to V-		44	V
GND to V-		25	
VL		(GND - 0.3 V) to (V+) + 0.3 V	
Digital inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first	
Continuous current (any terminal)		30	mA
Current, S or D (pulsed at 1 ms, 10 % duty cycle)		100	
Storage temperature		-65 to +125	°C
Power dissipation (package) ^b	16-pin narrow body SOIC ^d	640	mW
	QFN-16 ^e	850	

Notes

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 6 mW/°C above 75 °C
- d. Derate 8 mW/°C above 75 °C
- e. Derate 12 mW/°C above 75 °C

SPECIFICATIONS (for dual supplies)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V+ = 15 V, V- = -15 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^e	TEMP. ^a	D SUFFIX -40 °C TO +85 °C			UNIT
				MIN. ^b	TYP. ^c	MAX. ^b	
Analog Switch							
Analog signal range ^d	V _{ANALOG}		Full	-15	-	15	V
Drain-source on-resistance	R _{DS(on)}	I _S = 1 mA, V _D = ± 10 V	Room	-	45	80	Ω
			Full	-	-	95	
Switch off leakage current	I _{S(off)}	V _D = ± 14 V, V _S = ± 14 V	Room	- 0.5	± 0.01	0.5	nA
			Full	- 5	-	5	
	Room		- 0.5	± 0.01	0.5		
	Full		- 5	-	5		
Channel on leakage current	I _{D(on)}	V _S = V _D = ± 14 V	Room	-0.5	± 0.02	0.5	nA
			Full	-10	-	10	
Digital Control							
Input, low voltage	V _{INH}		Full	-	-	0.8	V
Input, high voltage	V _{INL}		Full	2.4	-	-	
Input current V _{IN} low	I _{INL}	V _{IN} under test = 0.8 V, all other = 2.4 V	Full	-1	- 0.01	1	μA
Input current V _{IN} high	I _{INH}	V _{IN} under test = 2.4 V, all other = 0.8 V	Full	-1	0.01	1	
Dynamic Characteristics							
Turn-on time	t _{on}	R _L = 1 kΩ, C _L = 35 pF, V _S = ± 10 V, See figure 2	Room	-	-	300	ns
Turn-off time	t _{off}		Room	-	-	200	
Charge Injection ^e	Q	C _L = 1 nF, V _S = 0 V, V _{gen} = 0 V, R _{gen} = 0 Ω	Room	-	1	-	pC
Off isolation ^e	OIRR	R _L = 50 Ω, C _L = 15 pF, v = 1 V _{RMS} , f = 100 kHz	Room	-	-90	-	dB
Crosstalk (channel-to-channel) ^d	X _{TALK}		Room	-	-95	-	
Source off capacitance	C _{S(off)}	V _S = 0 V, f = 100 kHz	Room	-	5	-	pF
Drain off capacitance	C _{D(off)}		Room	-	5	-	
Channel on capacitance	C _{D(on)}	V _S = V _D = 0 V, f = 1 MHz	Room	-	16	-	
Power Supplies							
Positive supply current	I+	V _{IN} = 0 V or 5 V	Room	-	-	1	μA
			Full	-	-	5	
Negative supply current	I-		Room	-1	-	-	
			Full	-5	-	-	
Logic supply current	I _{IN}		Room	-	-	1	
			Full	-	-	5	



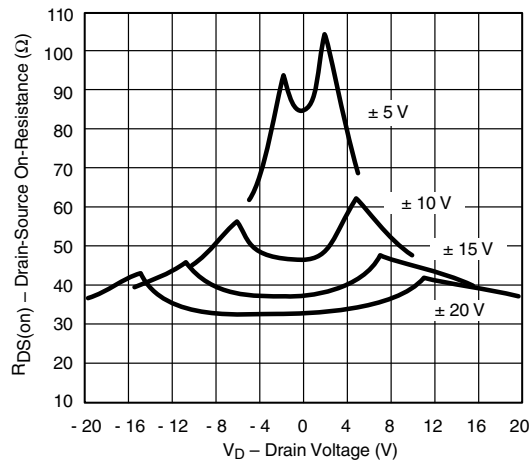
SPECIFICATIONS (for unipolar supplies)							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 12 V, V ₋ = 0 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^e	TEMP. ^a	D SUFFIX -40 °C TO +85 °C			UNIT
				MIN. ^b	TYP. ^c	MAX. ^b	
Analog Switch							
Analog signal range ^d	V _{ANALOG}		Full	0	-	12	V
Drain-source on-resistance ^d	R _{DS(on)}	I _S = 1 mA, V _D = 3 V, 8 V	Room	-	90	160	Ω
			Full	-	-	200	
Dynamic Characteristics							
Turn-on time	t _{on}	R _L = 1 kΩ, C _L = 35 pF, V _S = 8 V, See Fig. 2	Room	-	120	300	ns
Turn-off time	t _{off}		Room	-	60	200	
Charge Injection	Q	C _L = 1 nF, V _{gen} = 6 V, R _{gen} = 0 Ω	Room	-	4	-	pC
Power Supplies							
Positive supply current	I ₊	V _{IN} = 0 V or 5 V	Room	-	-	1	μA
			Full	-	-	5	
Negative supply current	I ₋		Room	-1	-	-	
			Full	-5	-	-	
Logic supply current	I _{IN}	V _L = 5.25 V, V _{IN} = 0 V or 5 V	Room	-	-	1	
			Full	-	-	5	

Notes

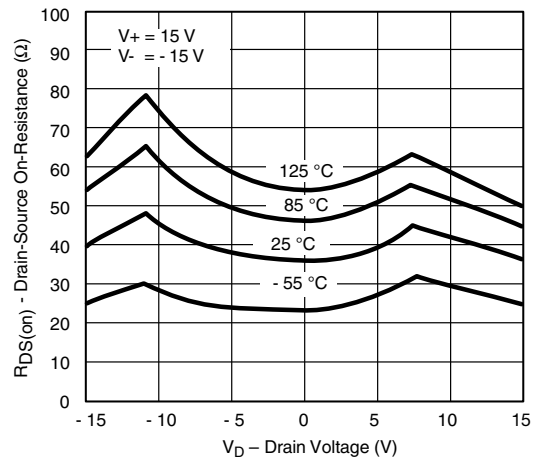
- a. Room = 25 °C, full = as determined by the operating temperature suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. Guaranteed by design, not subject to production test
- e. V_{IN} = input voltage to perform proper function

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



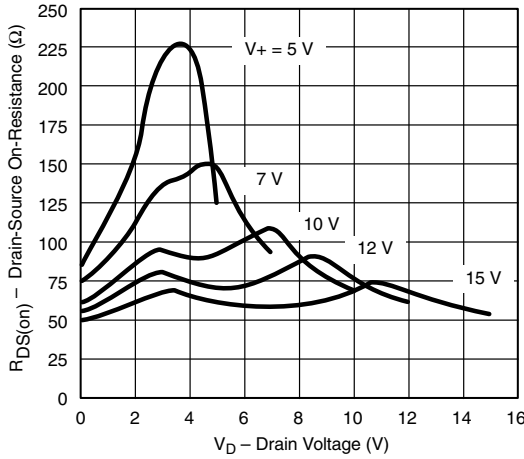
R_{DS(on)} vs. V_D and Power Supply Voltages



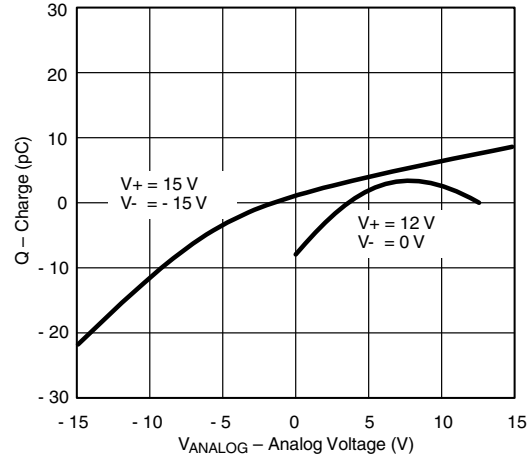
R_{DS(on)} vs. V_D and Temperature



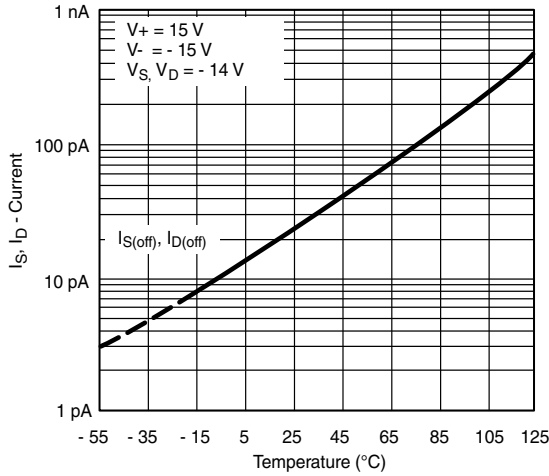
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



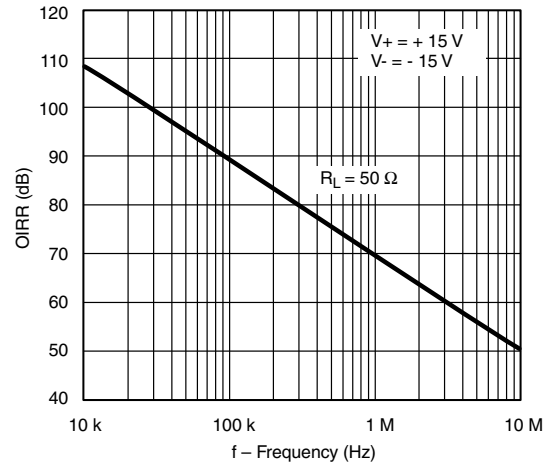
$R_{DS(on)}$ vs. V_D and Single Power Supply Voltages



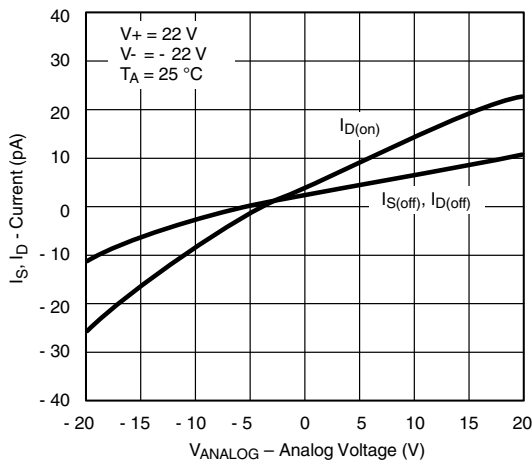
Q_S, Q_D - Charge Injection vs. Analog Voltage



Leakage Current vs. Temperature



Off Isolation vs. Frequency



Leakage Currents vs. Analog Voltage

SCHEMATIC DIAGRAM (typical channel)

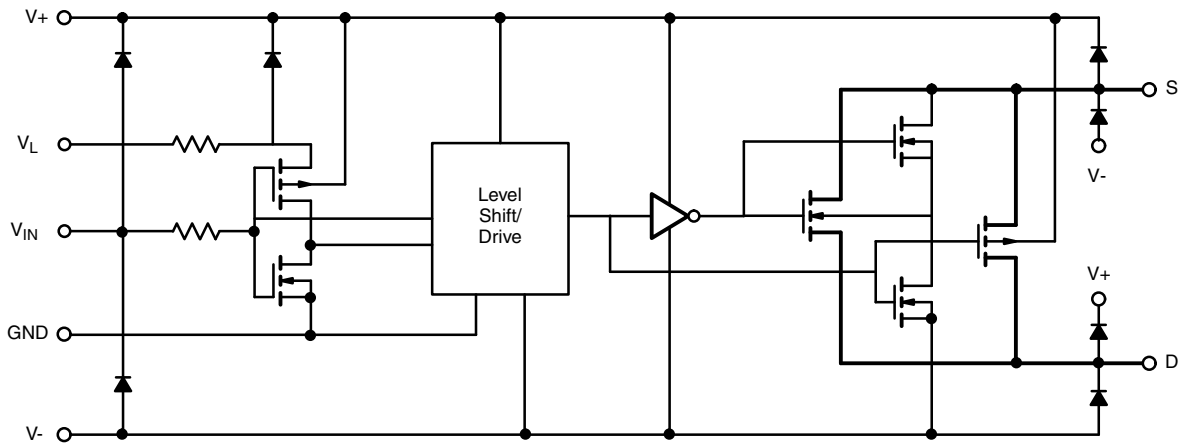
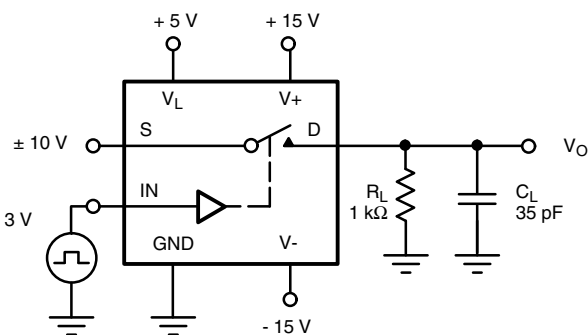
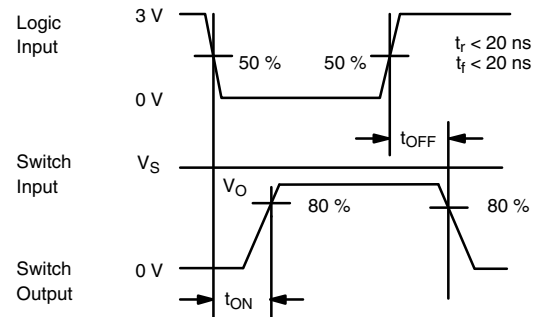


Fig. 1

TEST CIRCUITS



C_L (includes fixture and stray capacitance)



Note: Logic input waveform is inverted for DG445.

Fig. 2 - Switching Time

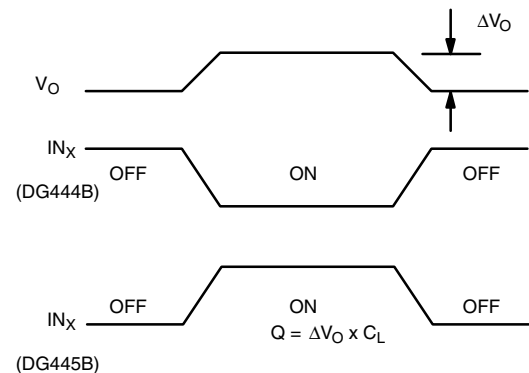
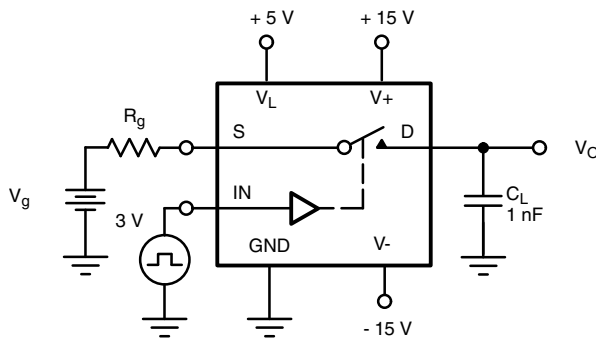


Fig. 3 - Charge Injection

TEST CIRCUITS

C = 1 mF tantalum in parallel with 0.01 mF ceramic

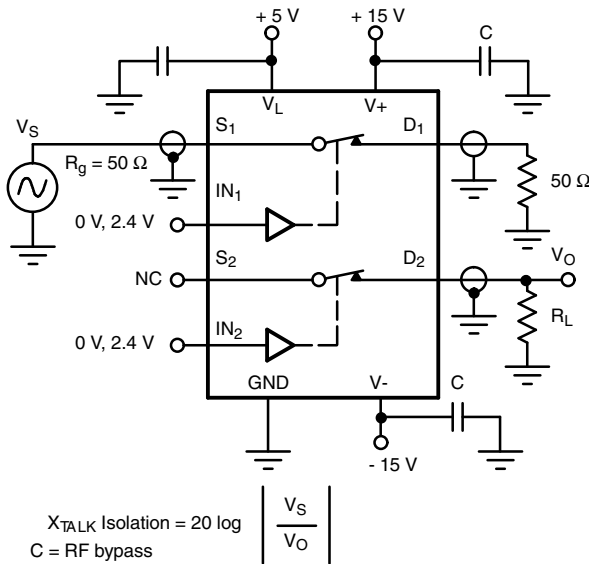


Fig. 4 - Crosstalk

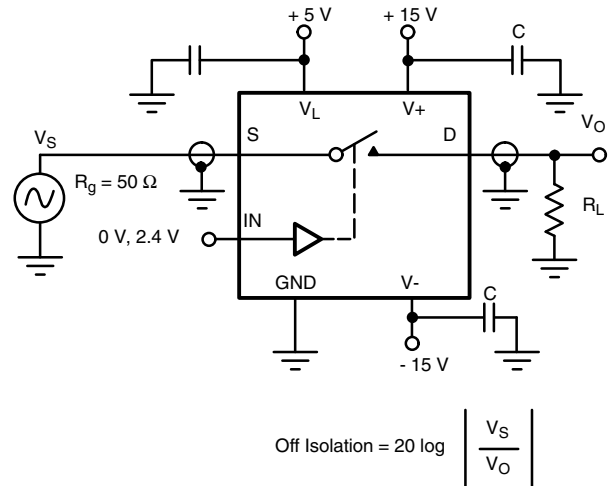


Fig. 5 - Off Isolation

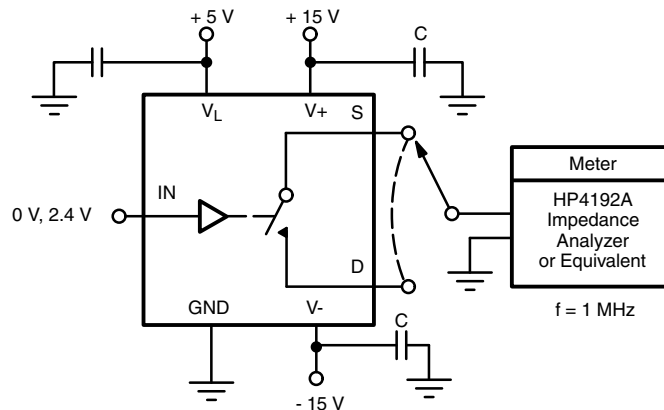


Fig. 6 - Source/Drain Capacitances

APPLICATIONS

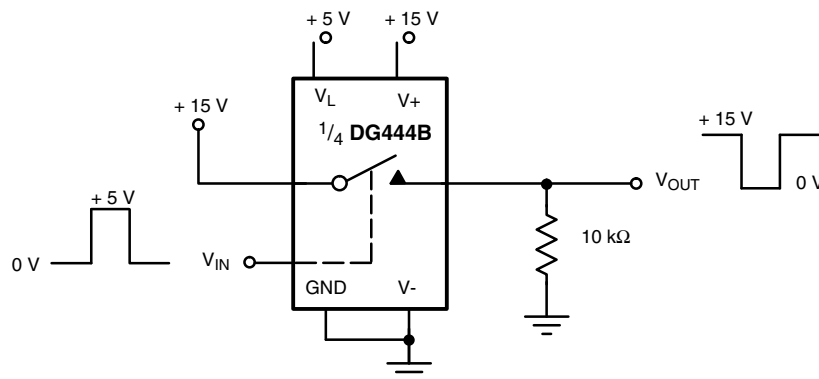


Fig. 7 - Level Shifter

APPLICATIONS

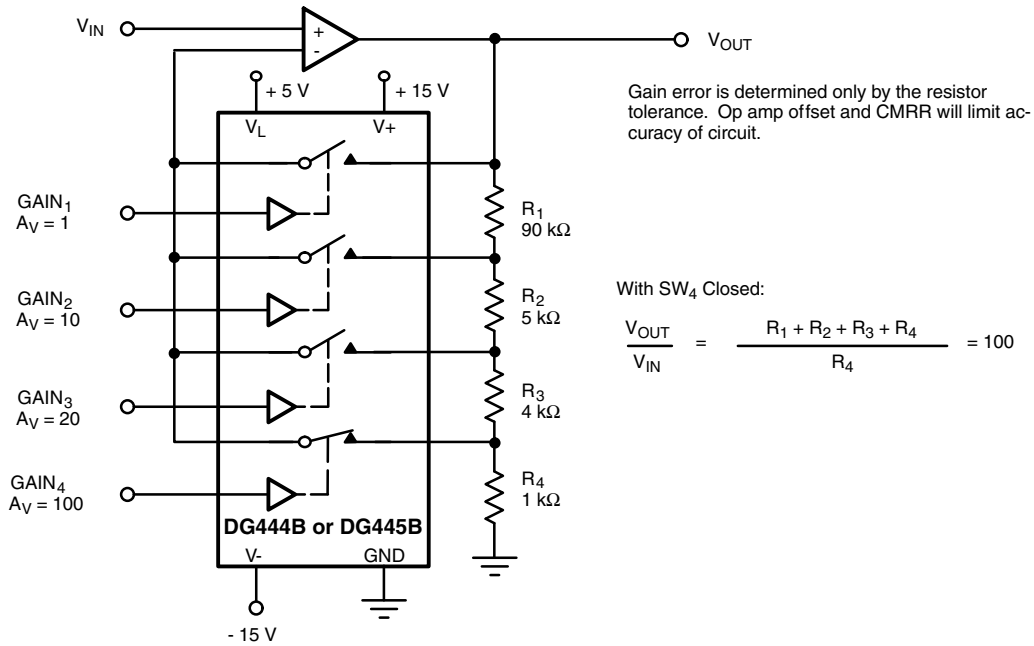


Fig. 8 - Precision-Weighted Resistor Programmable-Gain Amplifier

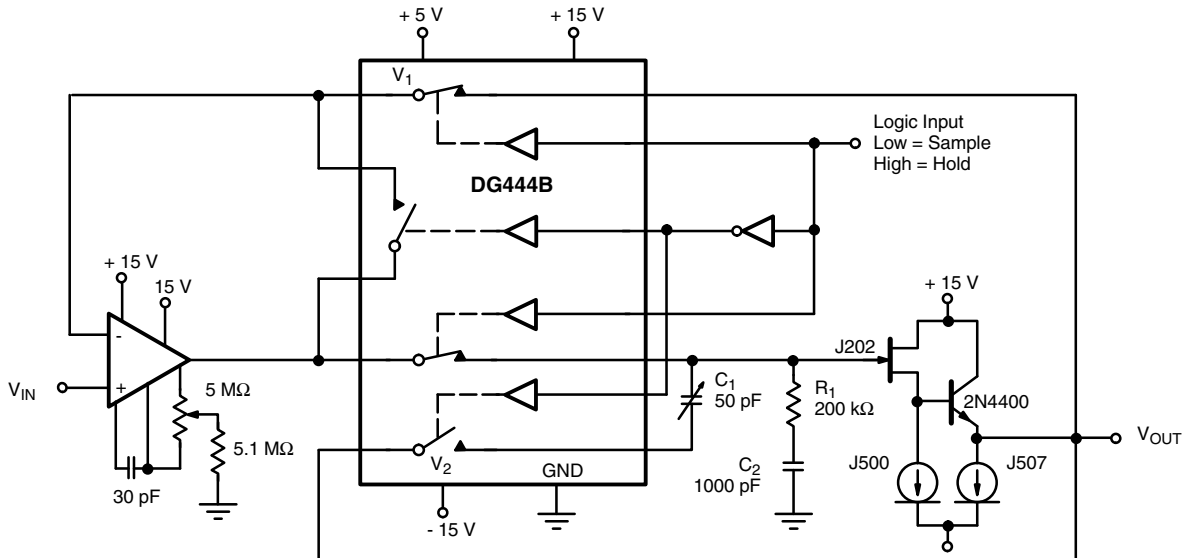


Fig. 9 - Precision Sample-and-Hold



PRODUCT SUMMARY				
Part number	DG444B	DG444B	DG445B	DG445B
Status code	2	2	2	2
Configuration	SPST x 4, NC	SPST x 4, NC	SPST x 4, NO	SPST x 4, NO
Single supply min. (V)	5	5	5	5
Single supply max. (V)	36	36	36	36
Dual supply min. (V)	5	5	5	5
Dual supply max. (V)	22	22	22	22
On-resistance (Ω)	45	45	45	45
Charge injection (pC)	1	1	1	1
Source on capacitance (pF)	16	16	16	16
Source off capacitance (pF)	5	5	5	5
Leakage switch on typ. (nA)	0.02	0.02	0.02	0.02
Leakage switch off max. (nA)	0.5	0.5	0.5	0.5
-3 dB bandwidth (MHz)	-	-	-	-
Package	SO-16 (narrow) AS	QFN-16 4 x 4	SO-16 (narrow) AS	QFN-16 4 x 4
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare	Multi purpose, instrumentation, medical and healthcare	Multi purpose, instrumentation, medical and healthcare	Multi purpose, instrumentation, medical and healthcare
Interface	Parallel	Parallel	Parallel	Parallel
Single supply operation	Yes	Yes	Yes	Yes
Dual supply operation	Yes	Yes	Yes	Yes
Turn on time max. (ns)	300	300	300	300
Crosstalk and off isolation	-90	-90	-90	-90

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SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012

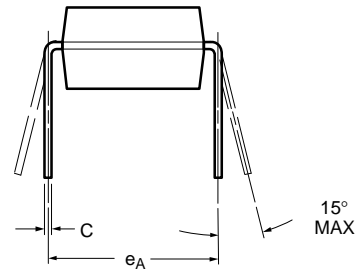


Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.38	0.51	0.015	0.020
C	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
∅	0°	8°	0°	8°

ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5300



PDIP: 16-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	3.81	5.08	0.150	0.200
A₁	0.38	1.27	0.015	0.050
B	0.38	0.51	0.015	0.020
B₁	0.89	1.65	0.035	0.065
C	0.20	0.30	0.008	0.012
D	18.93	21.33	0.745	0.840
E	7.62	8.26	0.300	0.325
E₁	5.59	7.11	0.220	0.280
e₁	2.29	2.79	0.090	0.110
e_A	7.37	7.87	0.290	0.310
L	2.79	3.81	0.110	0.150
Q₁	1.27	2.03	0.050	0.080
S	0.38	1.52	.015	0.060

ECN: S-03946—Rev. D, 09-Jul-01
DWG: 5482

QFN 4x4-16L Case Outline



DIM	VARIATION 1						VARIATION 2					
	MILLIMETERS ⁽¹⁾			INCHES			MILLIMETERS ⁽¹⁾			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3	0.20 ref.			0.008 ref.			0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
E	4.00 BSC			0.157 BSC			4.00 BSC			0.157 BSC		
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
K	0.20 min.			0.008 min.			0.20 min.			0.008 min.		
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N ⁽³⁾	16			16			16			16		
Nd ⁽³⁾	4			4			4			4		
Ne ⁽³⁾	4			4			4			4		

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13
 DWG: 5890

RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads
Dimensions in Inches/(mm)

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